Dual 4-input NAND gate Rev. 4 — 18 November 2015

1. **General description**

The 74HC20; 74HCT20 is a dual 4-input NAND gate. Inputs include clamp diodes. This enables the use of current limiting resistors to interface inputs to voltages in excess of V_{CC}.

Features and benefits 2.

- Complies with JEDEC standard JESD7A
- Low-power dissipation
- Input levels:
 - For 74HC20: CMOS level
 - For 74HCT20: TTL level
- ESD protection:
 - HBM JESD22-A114F exceeds 2000 V
 - MM JESD22-A115-A exceeds 200 V
- Multiple package options
- Specified from -40 °C to +80 °C and from -40 °C to +125 °C.

Ordering information 3.

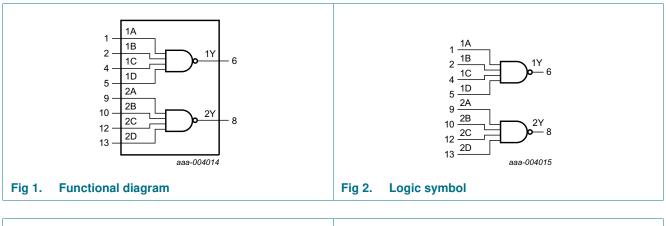
Table 1. **Ordering information**

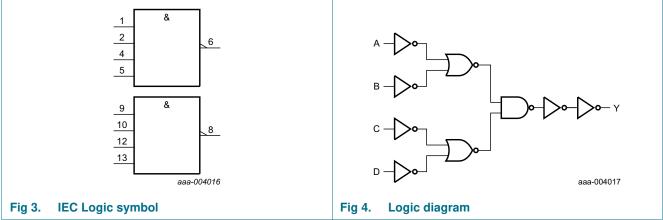
Type number	Package			
	Temperature range	Name	Description	Version
74HC20D	–40 °C to +125 °C	SO14	plastic small outline package; 14 leads; body width	SOT108-1
74HCT20D			3.9 mm	
74HC20DB	–40 °C to +125 °C	SSOP14	plastic shrink small outline package; 14 leads; body	SOT337-1
74HCT20DB			width 5.3 mm	
74HC20PW	–40 °C to +125 °C	TSSOP14	plastic thin shrink small outline package; 14 leads;	SOT402-1
74HCT20PW			body width 4.4 mm	



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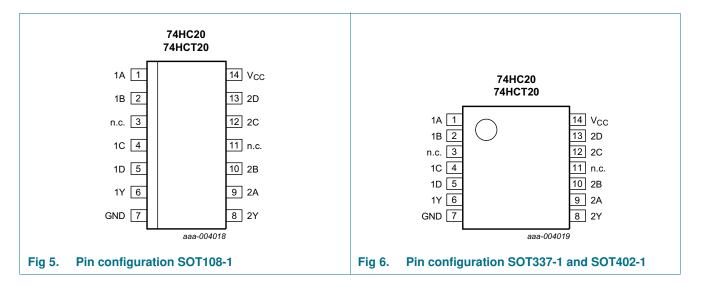
4. Functional diagram





5. Pinning information

5.1 Pinning



5.2 Pin description

Table 2. Pin description							
Symbol	Pin	Description					
1A, 1B, 1C, 1D	1, 2, 4, 5	data input					
n.c.	3, 11	not connected					
1Y	6	data output					
GND	7	ground (0 V)					
2Y	8	data output					
2A, 2B, 2C, 2D	9, 10, 12, 13	data input					
V _{CC}	14	supply voltage					

6. Functional description

Table 3. Function table^[1]

Input	Output			
nA	nB	nC	nD	nY
L	Х	Х	Х	Н
Х	L	Х	Х	Н
Х	Х	L	Х	Н
Х	Х	Х	L	Н
Н	Н	Н	Н	L

[1] H = HIGH voltage level; L = LOW voltage level; X = don't care.

7. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions		Min	Max	Unit
V _{CC}	supply voltage			-0.5	+7	V
I _{IK}	input clamping current	$V_{I} < -0.5 \text{ V or } V_{I} > V_{CC} + 0.5 \text{ V}$	<u>[1]</u>	-	±20	mA
I _{OK}	output clamping current	$V_O < -0.5$ V or $V_O > V_{CC}$ + 0.5 V	<u>[1]</u>	-	±20	mA
lo	output current	$-0.5 \text{ V} < \text{V}_{\text{O}} < \text{V}_{\text{CC}} + 0.5 \text{ V}$		-	±25	mA
I _{CC}	supply current			-	50	mA
I _{GND}	ground current			-50	-	mA
T _{stg}	storage temperature			-65	+150	°C
P _{tot}	total power dissipation	SO14, and (T)SSOP14 packages	[2]	-	500	mW

[1] The input and output voltage ratings may be exceeded if the input and output current ratings are observed.

For SO14 package: P_{tot} derates linearly with 8 mW/K above 70 °C.
 For (T)SSOP14 packages: P_{tot} derates linearly with 5.5 mW/K above 60 °C.

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8. Recommended operating conditions

Table 5. Recommended operating conditions

Voltages are referenced to GND (ground = 0 V)

Symbol	Parameter	Conditions		74HC20			74HCT20	כ	Unit
			Min	Тур	Max	Min	Тур	Max	
V _{CC}	supply voltage		2.0	5.0	6.0	4.5	5.0	5.5	V
VI	input voltage		0	-	V _{CC}	0	-	V _{CC}	V
Vo	output voltage		0	-	V _{CC}	0	-	V _{CC}	V
T _{amb}	ambient temperature		-40	+25	+125	-40	+25	+125	°C
$\Delta t / \Delta V$	input transition rise and fall rate	$V_{CC} = 2.0 V$	-	-	625	-	-	-	ns/V
		$V_{CC} = 4.5 V$	-	1.67	139	-	1.67	139	ns/V
		$V_{CC} = 6.0 V$	-	-	83	-	-	-	ns/V

9. Static characteristics

Table 6. Static characteristics

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions		25 °C		–40 °C t	o +85 °C	–40 °C to	+125 °C	Unit
			Min	Тур	Max	Min	Max	Min	Max	
74HC20	1									
V _{IH}	HIGH-level	V _{CC} = 2.0 V	1.5	1.2	-	1.5	-	1.5	-	V
	input voltage	V _{CC} = 4.5 V	3.15	2.4	-	3.15	-	3.15	-	V
		V _{CC} = 6.0 V	4.2	3.2	-	4.2	-	4.2	-	V
V _{IL}	LOW-level	V _{CC} = 2.0 V	-	0.8	0.5	-	0.5	-	0.5	V
	input voltage	V _{CC} = 4.5 V	-	2.1	1.35	-	1.35	-	1.35	V
		V _{CC} = 6.0 V	-	2.8	1.8	-	1.8	-	1.8	V
V _{OH}	HIGH-level	$V_{I} = V_{IH} \text{ or } V_{IL}$								
	output voltage	$I_{O} = -20 \ \mu A; \ V_{CC} = 2.0 \ V$	1.9	2.0	-	1.9	-	1.9	-	V
		$I_{O} = -20 \ \mu A; \ V_{CC} = 4.5 \ V$	4.4	4.5	-	4.4	-	4.4	-	V
		$I_O = -20 \ \mu\text{A}; \ V_{CC} = 6.0 \ \text{V}$	5.9	6.0	-	5.9	-	5.9	-	V
		$I_{O} = -4.0 \text{ mA}; V_{CC} = 4.5 \text{ V}$	3.98	4.32	-	3.84	-	3.7	-	V
		$I_{O} = -5.2 \text{ mA}; V_{CC} = 6.0 \text{ V}$	5.48	5.81	-	5.34	-	5.2	-	V
V _{OL}	LOW-level	$V_I = V_{IH} \text{ or } V_{IL}$								
	output voltage	$I_{O} = 20 \ \mu A; \ V_{CC} = 2.0 \ V$	-	0	0.1	-	0.1	-	0.1	V
		$I_{O} = 20 \ \mu A; V_{CC} = 4.5 \ V$	-	0	0.1	-	0.1	-	0.1	V
		$I_{O} = 20 \ \mu A; V_{CC} = 6.0 \ V$	-	0	0.1	-	0.1	-	0.1	V
		$I_{O} = 4.0 \text{ mA}; V_{CC} = 4.5 \text{ V}$	-	0.15	0.26	-	0.33	-	0.4	V
		$I_{O} = 5.2 \text{ mA}; V_{CC} = 6.0 \text{ V}$	-	0.16	0.26	-	0.33	-	0.4	V
lı	input leakage current		-	-	±0.1	-	±1	-	±1	μA
I _{CC}	supply current		-	-	2	-	20	-	40	μA

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Table 6. Static characteristics ...continued

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions		25 °C		–40 °C t	o +85 °C	–40 °C t	o +125 °C	pF ν ν ν ν ν ν ν μΑ
			Min	Тур	Max	Min	Max	Min	Max	
CI	input capacitance		-	3.5	-	-	-	-	-	pF
74HCT2	0						1	1		1
V _{IH}	HIGH-level input voltage	nput voltage		1.6	-	2.0	-	2.0	-	V
V _{IL}	LOW-level input voltage	88		1.2	0.8	-	0.8	-	0.8	V
V _{OH} HIGH-level output voltage	$V_{I} = V_{IH} \text{ or } V_{IL}; V_{CC} = 4.5 \text{ V}$									
	I _O = -20 μA	4.4	4.5	-	4.4	-	4.4	-	V	
		$I_{O} = -4.0 \text{ mA}$	3.98	4.32	-	3.84	-	3.7	-	V
0L	LOW-level	$V_{I} = V_{IH} \text{ or } V_{IL}; V_{CC} = 4.5 \text{ V}$								
	output voltage	I _O = 20 μA	-	0	0.1	-	0.1	-	0.1	V
		I _O = 5.2 mA	-	0.15	0.26	-	0.33	-	0.4	V
I _I	input leakage current	$V_I = V_{CC}$ or GND; $V_{CC} = 5.5 V$	-	-	±0.1	-	±1	-	±1	μA
I _{CC}	supply current		-	-	2	-	20	-	40	μA
ΔI _{CC}	additional supply current	per input pin; $V_I = V_{CC} - 2.1 \text{ V}; I_O = 0 \text{ A};$ other inputs at V_{CC} or GND; $V_{CC} = 4.5 \text{ V}$ to 5.5 V	-	30	108	-	135	-	147	μA
Cı	input capacitance		-	3.5	-	-	-	-	-	pF

Dual 4-input NAND gate

10. Dynamic characteristics

Table 7. Dynamic characteristics

 $GND = 0 V; C_L = 50 pF;$ for test circuit see <u>Figure 8</u>.

Symbol	Parameter	Conditions			25 °C		–40 °C to	o +125 ℃	Unit
				Min	Тур	Max	Max (85 °C)	Max (125 °C)	_
74HC20									
t _{pd}	propagation delay	nA, nB, nC or nD to nY; see <u>Figure 7</u>	<u>[1]</u>						
		V _{CC} = 2.0 V		-	28	90	115	135	ns
		V _{CC} = 4.5 V		-	10	18	23	27	ns
		V _{CC} = 6.0 V		-	8	15	20	23	ns
		V _{CC} = 5.0 V; C _L = 15 pF		-	8	-	-	-	ns
t _t	transition time	see <u>Figure 7</u>	[2]						
		V _{CC} = 2.0 V		-	19	75	95	110	ns
		V _{CC} = 4.5 V		-	7	15	19	22	ns
		V _{CC} = 6.0 V		-	6	13	16	19	ns
C _{PD}	power dissipation capacitance	per package; $V_I = GND$ to V_{CC}	<u>[3]</u>	-	22	-	-	-	pF
74HCT20)								
t _{pd}	propagation delay	nA, nB, nC or nD to nY; see <u>Figure 7</u>	<u>[1]</u>						
		V _{CC} = 4.5 V		-	16	28	35	42	ns
		V _{CC} = 5.0 V; C _L = 15 pF		-	13	-	-	-	ns
t _t	transition time	$V_{CC} = 4.5 \text{ V}; \text{ see } \frac{\text{Figure 7}}{1000}$	[2]	-	7	15	19	22	ns
C _{PD}	power dissipation capacitance	per package; V _I = GND to V _{CC} – 1.5 V	<u>[3]</u>	-	17	-	-	-	pF

[1] t_{pd} is the same as t_{PHL} and t_{PLH} .

 $\label{eq:ttilde} [2] \quad t_t \text{ is the same as } t_{THL} \text{ and } t_{TLH}.$

[3] C_{PD} is used to determine the dynamic power dissipation (P_D in μ W):

 $P_{D} = C_{PD} \times V_{CC}^{2} \times f_{i} \times N + \sum (C_{L} \times V_{CC}^{2} \times f_{o}) \text{ where:}$

 f_i = input frequency in MHz;

 $f_o = output frequency in MHz;$

 C_L = output load capacitance in pF;

V_{CC} = supply voltage in V;

N = number of inputs switching;

 $\Sigma~(C_L \times V_{CC}{}^2 \times f_o)$ = sum of outputs.

Dual 4-input NAND gate

11. Waveforms

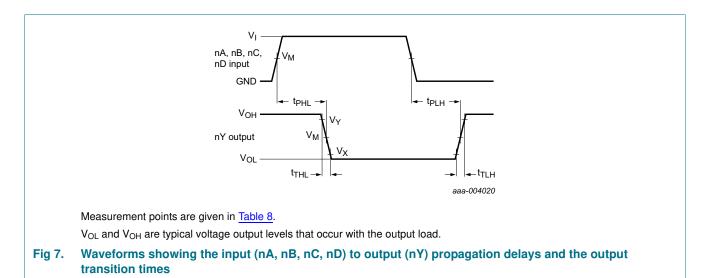


Table 8. Measurement points

Туре	Input	Output				
	V _M	V _M V _X V _Y				
74HC20	0.5V _{CC}	0.5V _{CC}	0.1V _{CC}	0.9V _{CC}		
74HCT20	1.3 V	1.3 V	0.1V _{CC}	0.9V _{CC}		

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74HC20; 74HCT20

Dual 4-input NAND gate

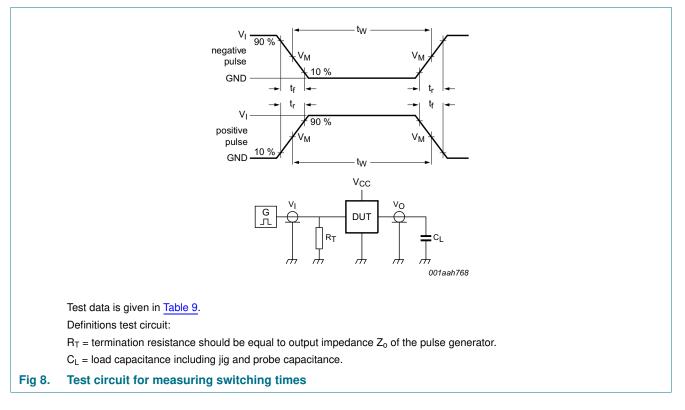


Table 9. Test data

Туре	Input Lo		Load	Test
	VI	t _r , t _f	CL	
74HC20	V _{CC}	6.0 ns	15 pF, 50 pF	t _{PLH} , t _{PHL}
74HCT20	3.0 V	6.0 ns	15 pF, 50 pF	t _{PLH} , t _{PHL}

Dual 4-input NAND gate

12. Package outline

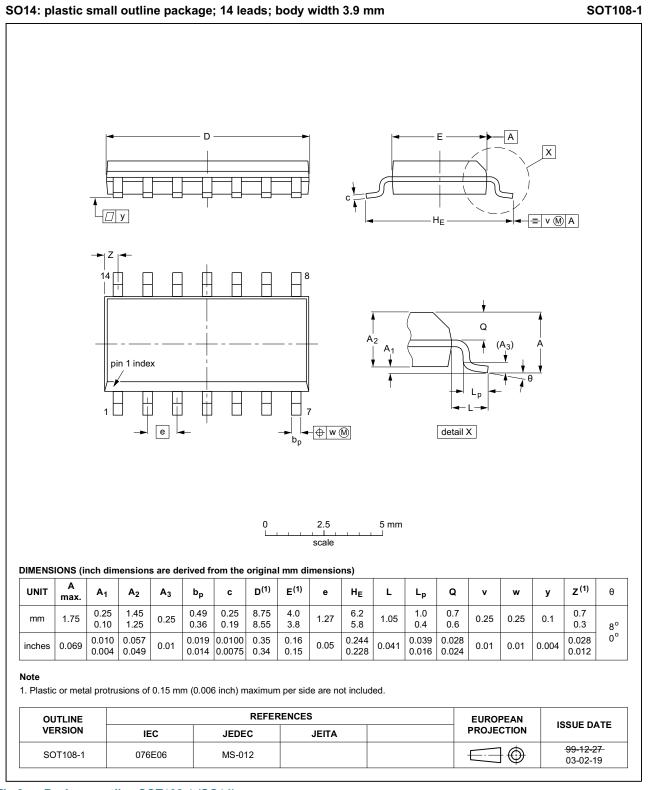


Fig 9. Package outline SOT108-1 (SO14)

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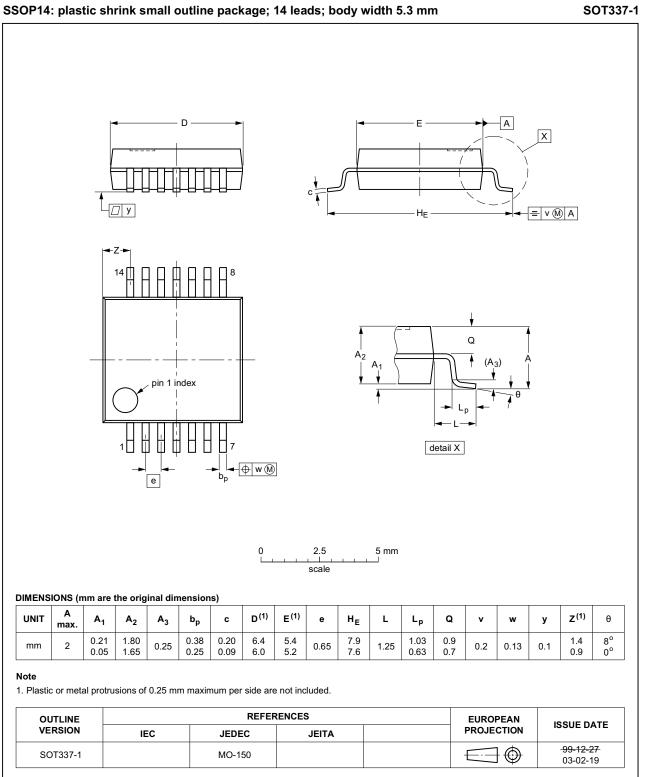


Fig 10. Package outline SOT337-1 (SSOP14)

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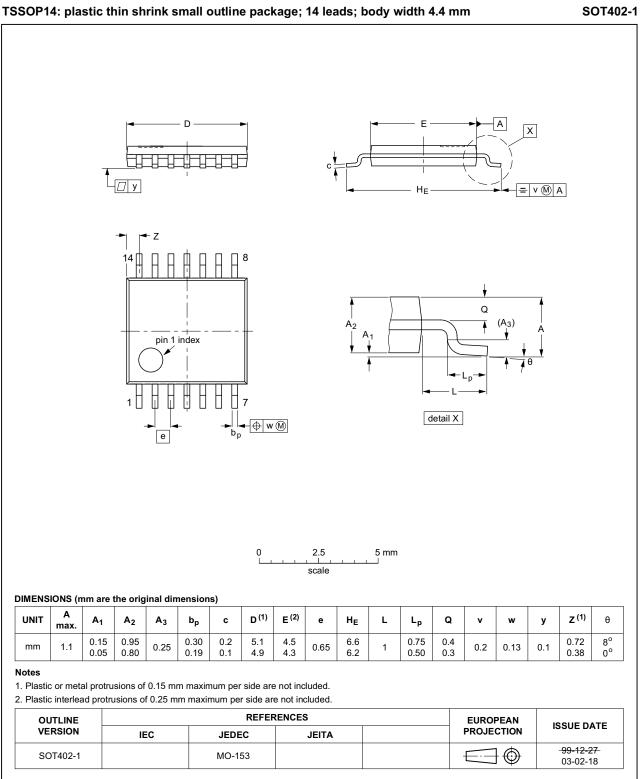


Fig 11. Package outline SOT402-1 (TSSOP14)

74HC_HCT20

13. Abbreviations

Table 10. Abbreviations						
Acronym	Description					
CMOS	Complementary Metal Oxide Semiconductor					
DUT	Device Under Test					
ESD	ElectroStatic Discharge					
НВМ	Human Body Model					
MM	Machine Model					
TTL	Transistor-Transistor Logic					

14. Revision history

Table 11. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes	
74HC_HCT20 v.4	20151118	Product data sheet	-	74HC_HCT20 v.3	
Modifications:	Type number	ers 74HC20N and 74HCT20	N (SOT27-1) removed		
74HC_HCT20 v.3	20120903	Product data sheet	-	74HC_HCT20_CNV v.2	
Modifications:		of this data sheet has been r niconductors.	redesigned to comply w	ith the new identity guidelines	
	Legal texts have been adapted to the new company name where appropriate.				
74HC_HCT20_CNV v.2	19970828	Product specification	-	74HC_HCT20_1	

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Document status[1][2]	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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Product [short] data sheet	Production	This document contains the product specification.

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